

## Dual N-Channel 40-V MOSFET

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	r <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A)	Q <sub>g</sub> (Typ)
40	0.016 at V <sub>GS</sub> = 10 V	8	56
	0.019 at V <sub>GS</sub> = 4.5 V	8	

### FEATURES

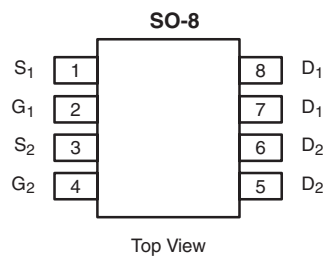
- TrenchFET<sup>®</sup> Power MOSFET
- 100 % R<sub>g</sub> Tested
- UIS Tested



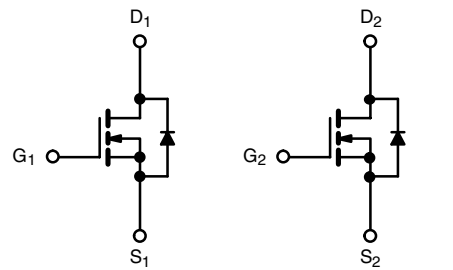
**RoHS**  
COMPLIANT

### APPLICATIONS

- CCFL Inverter



Ordering Information: Si4904DY-T1-E3 (Lead (Pb)-free)



N-Channel MOSFET

N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T <sub>A</sub> = 25 °C, unless otherwise noted				
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V <sub>DS</sub>	40	V	
Gate-Source Voltage	V <sub>GS</sub>	± 16		
Continuous Drain Current (T <sub>J</sub> = 150 °C)	I <sub>D</sub>	T <sub>C</sub> = 25 °C	8	
		T <sub>C</sub> = 70 °C	8	
		T <sub>A</sub> = 25 °C	8 <sup>b, c</sup>	
		T <sub>A</sub> = 70 °C	6.5 <sup>b, c</sup>	
Pulsed Drain Current (10 μs Pulse Width)	I <sub>DM</sub>	20	A	
Source-Drain Current Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C		2.7
		T <sub>A</sub> = 25 °C		1.6 <sup>b, c</sup>
Pulsed Source-Drain Current	I <sub>SM</sub>	20		
Single Pulse Avalanche Current	I <sub>AS</sub>	20		
Single Pulse Avalanche Energy	E <sub>AS</sub>	20		
Maximum Power Dissipation	P <sub>D</sub>	T <sub>C</sub> = 25 °C	3.25	
		T <sub>C</sub> = 70 °C	2.10	
		T <sub>A</sub> = 25 °C	2.0 <sup>b, c</sup>	
		T <sub>A</sub> = 70 °C	1.25 <sup>b, c</sup>	
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150	°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typ	Max	Unit	
Maximum Junction-to-Ambient <sup>b, d</sup>	R <sub>thJA</sub>	45	62.5	°C/W	
Maximum Junction-to-Foot (Drain)	R <sub>thJF</sub>	29	38		

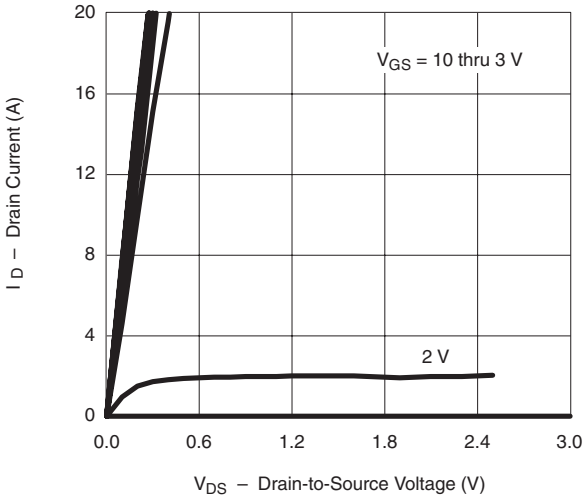
Notes:

- Based on T<sub>C</sub> = 25 °C.
- Surface Mounted on 1" x 1" FR4 Board.
- t = 10 s.
- Maximum under steady state conditions is 120 °C/W.

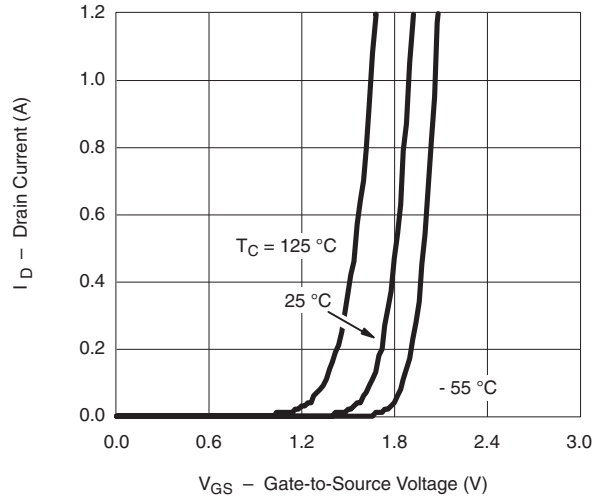
<b>SPECIFICATIONS</b> $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	40			V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\text{ }\mu\text{A}$		40		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	$I_D = 250\text{ }\mu\text{A}$		- 4.8		
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	0.8		2.0	V
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 16\text{ V}$			100	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 40\text{ V}, V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
		$V_{DS} = 40\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			10	
On -State Drain Current <sup>b</sup>	$I_{D(on)}$	$V_{DS} = 5\text{ V}, V_{GS} = 10\text{ V}$	20			A
Drain-Source On-State Resistance <sup>b</sup>	$r_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 5\text{ A}$		0.013	0.016	$\Omega$
		$V_{GS} = 4.5\text{ V}, I_D = 4\text{ A}$		0.015	0.019	
Forward Transconductance <sup>b</sup>	$g_{fs}$	$V_{DS} = 15\text{ V}, I_D = 5\text{ A}$		23		S
<b>Dynamic<sup>a</sup></b>						
Input Capacitance	$C_{iss}$	N-Channel $V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}, I_D = 1\text{ MHz}$		2390		pF
Output Capacitance	$C_{oss}$			270		
Reverse Transfer Capacitance	$C_{rss}$			165		
Total Gate Charge	$Q_g$	N-Channel $V_{DS} = 20\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 5\text{ A}$	$V_{DS} = 20\text{ V}, V_{GS} = 10\text{ V}, I_D = 5\text{ A}$	56	85	nC
				26	40	
Gate-Source Charge	$Q_{gs}$		5.5			
Gate-Drain Charge	$Q_{gd}$		9.7			
Gate Resistance	$R_g$	$f = 1\text{ MHz}$		2.6	4.0	
Turn-On Delay Time	$t_{d(on)}$	N-Channel $V_{DD} = 20\text{ V}, R_L = 4\text{ }\Omega$ $I_D \cong 5\text{ A}, V_{GEN} = 4.5\text{ V}, R_G = 1\text{ }\Omega$		15	23	ns
Rise Time	$t_r$			20	30	
Turn-Off Delay Time	$t_{d(off)}$			56	85	
Fall Time	$t_f$			10	15	
Turn-On Delay Time	$t_{d(on)}$	N-Channel $V_{DD} = 20\text{ V}, R_L = 4\text{ }\Omega$ $I_D \cong 5\text{ A}, V_{GEN} = 4.5\text{ V}, R_G = 1\text{ }\Omega$		88	135	
Rise Time	$t_r$			117	180	
Turn-Off Delay Time	$t_{d(off)}$			62	95	
Fall Time	$t_f$			19	30	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Source-Drain Diode Current	$I_S$	$T_C = 25\text{ }^\circ\text{C}$			2.7	A
Pulse Diode Forward Current <sup>a</sup>	$I_{SM}$				20	
Body Diode Voltage	$V_{SD}$	$I_S = 1.5\text{ A}$		0.69	1.2	V
Body Diode Reverse Recovery Time	$t_{rr}$	N-Channel $I_F = 2\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		62	95	ns
Body Diode Reverse Recovery Charge	$Q_{rr}$			62	95	nC
Reverse Recovery Fall Time	$t_a$			26		nS
Reverse Recovery Rise Time	$t_b$			36		

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

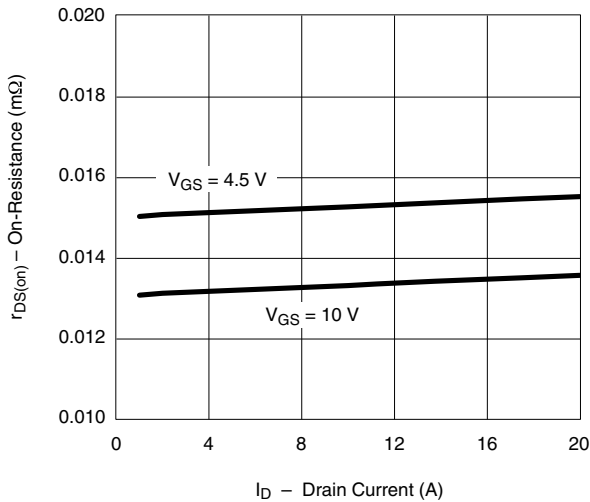
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



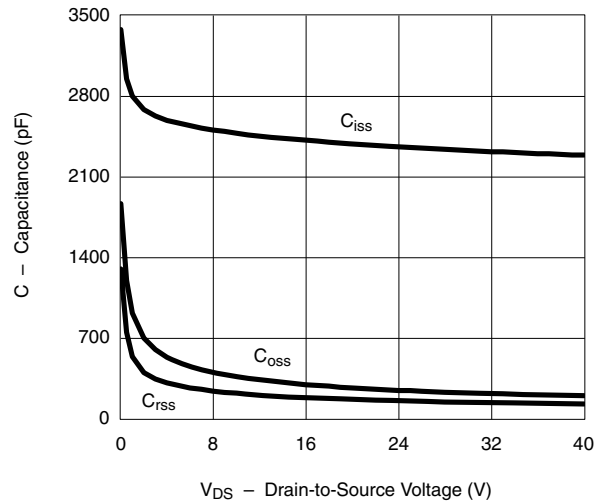
**Output Characteristics**



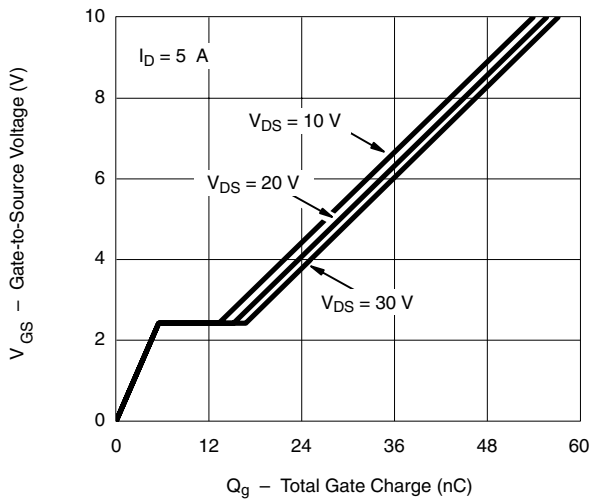
**Transfer Characteristics**



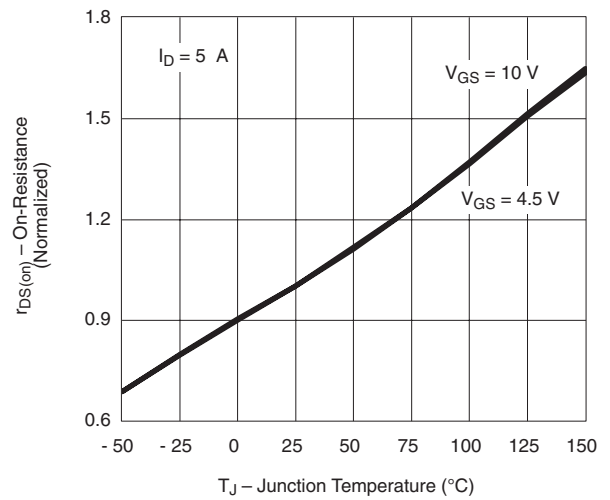
**On-Resistance vs. Drain Current and Gate Voltage**



**Capacitance**

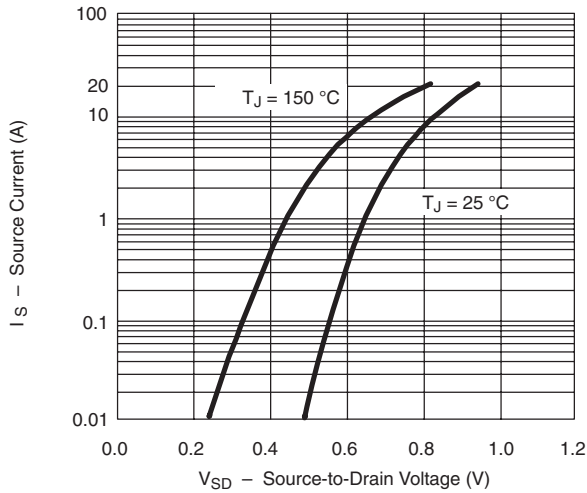


**Gate Charge**

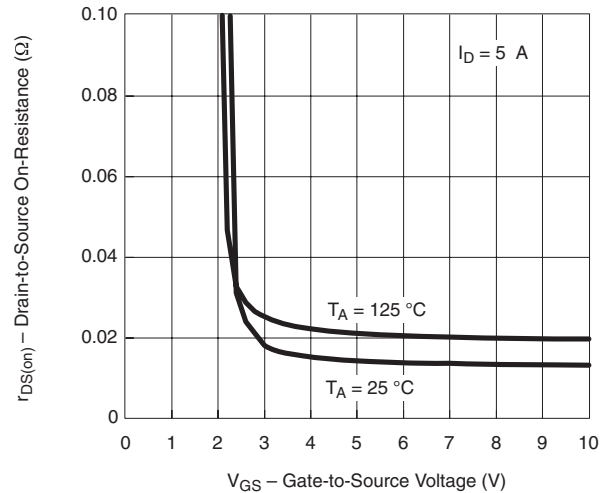


**On-Resistance vs. Junction Temperature**

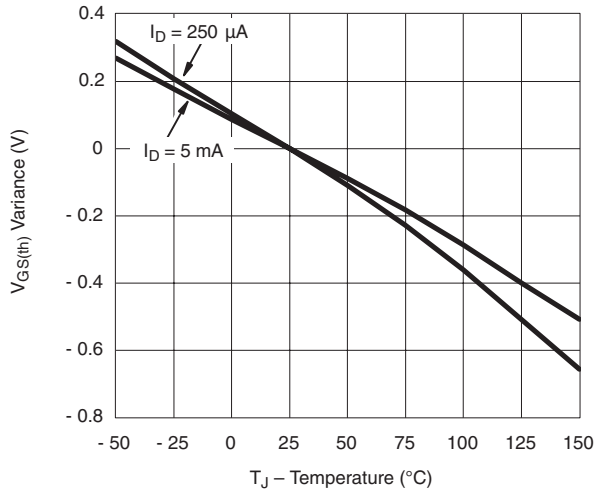
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



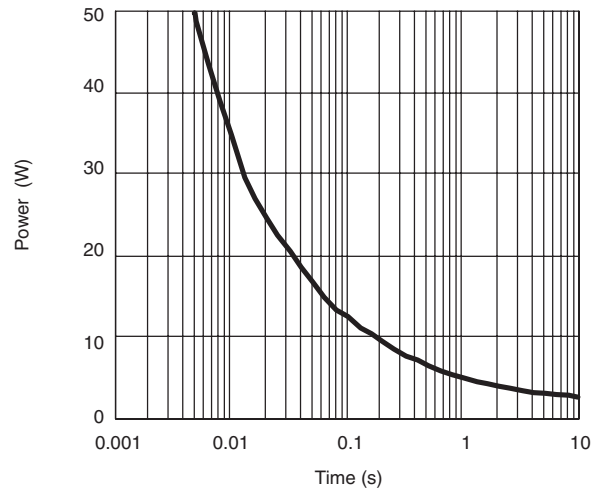
**Source-Drain Diode Forward Voltage**



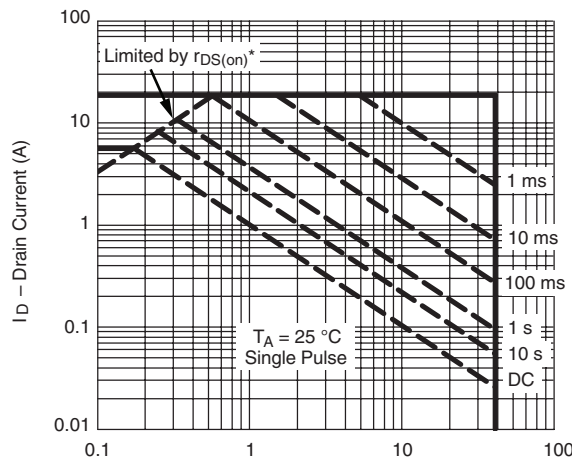
**On-Resistance vs. Gate-to-Source Voltage**



**Threshold Voltage**



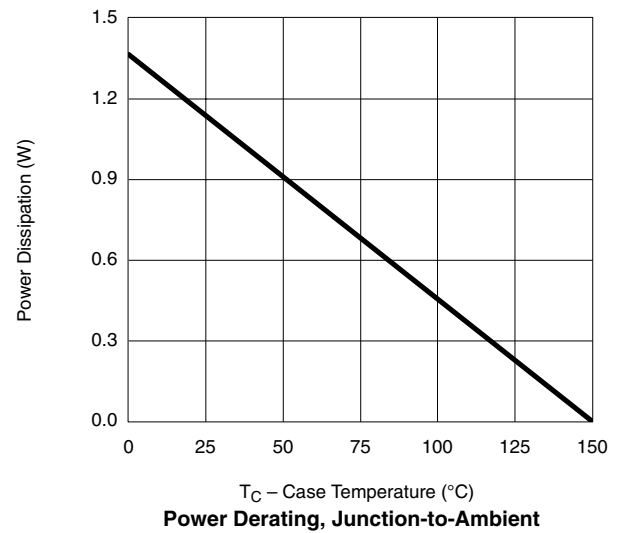
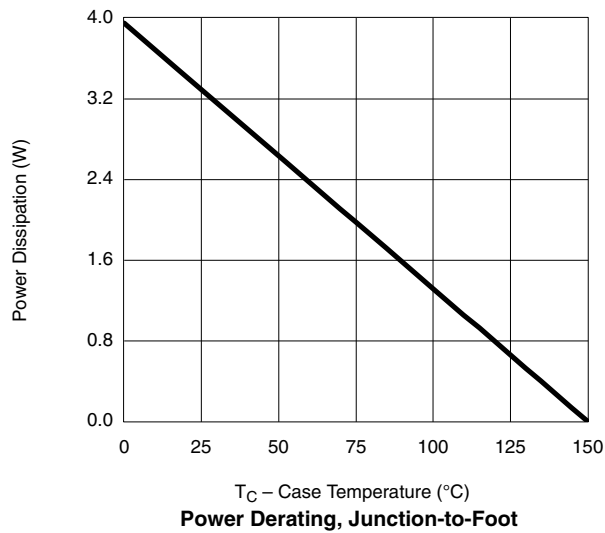
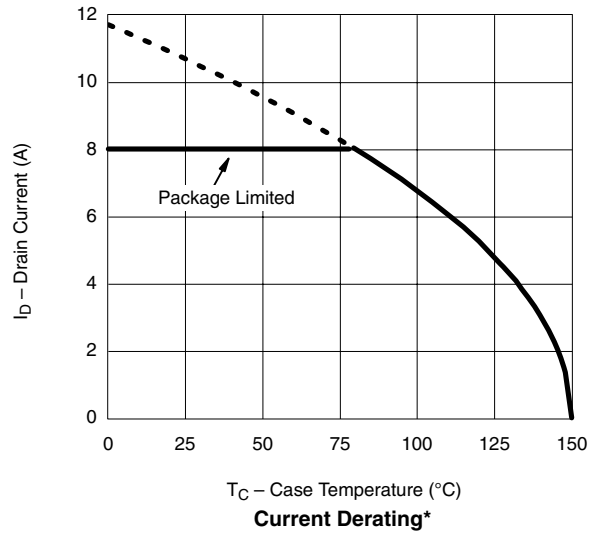
**Single Pulse Power, Junction-to-Ambient**



\*  $V_{GS} >$  minimum  $V_{GS}$  at which  $r_{DS(on)}$  is specified

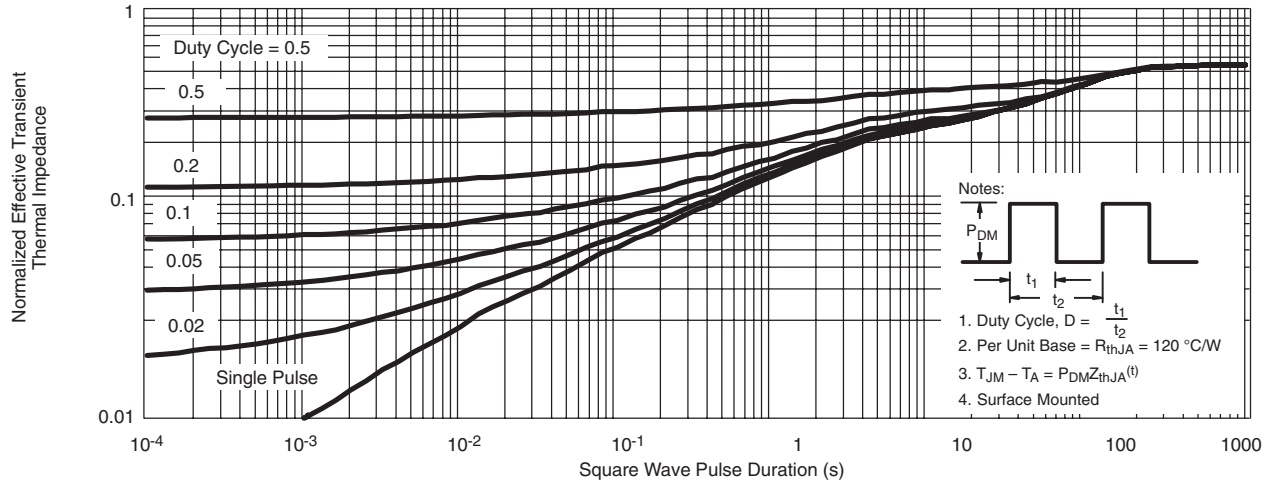
**Safe Operating Area, Junction-to-Ambient**

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted

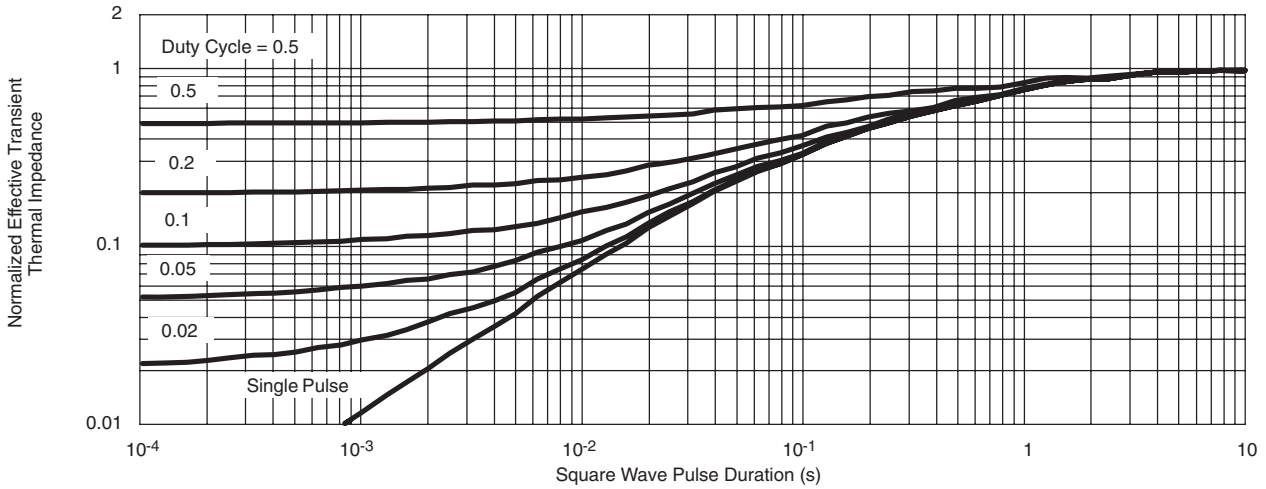


\* The power dissipation P<sub>D</sub> is based on T<sub>J(max)</sub> = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



**Normalized Thermal Transient Impedance, Junction-to-Ambient**



**Normalized Thermal Transient Impedance, Junction-to-Case**

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